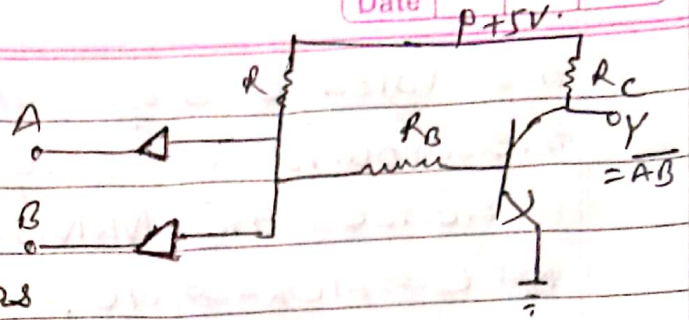


DTL NAND gate :



The ckt diagram for the DTL NAND gate has been shown in the fig.

Let us take the truth table the ckt operation has been described below :



| A | B | Y |
|---|---|---|
| 0 | 0 | 1 |
| 0 | 1 | 1 |
| 1 | 0 | 1 |
| 1 | 1 | 0 |

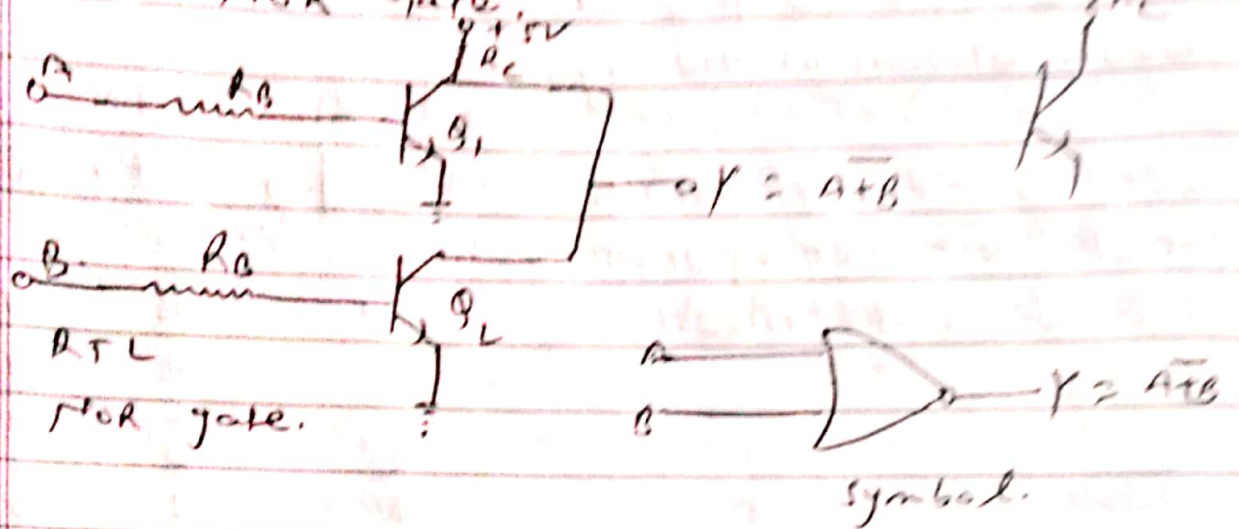
When both A and B inputs are low, both the diodes are forward biased and the supply +5V passes through them to the ground. Hence there is no voltage drop across  $R_B$ , the transistor remains unbiased and hence the voltage drop across  $R_C$  appears in the output as  $Y = 1$ . For the entries  $A = 0, B = 1$ ; The voltage drops across R. Hence no voltage drop across  $R_B$ , the transistor remains off and the voltage drop across  $R_C$  appears in the output yielding  $Y = 1$ . For  $A = 1, B = 0$ , the similar case as explained above in the 2<sup>nd</sup> entry happens and  $Y = 1$ . For the last entry  $A = 1, B = 1$ , both the diodes are reverse biased. There is voltage drop across  $R_B$ , the transistor is biased, it conducts and hence



the voltage drop across  $R_C$  by passes to the ground yielding  $Y=0$ .

Hence the NAND gate

RTL NOR Gate:



The RTL ckt for the NOR gate has been outlined in the fig. The truth table for the NOR gate is given below:

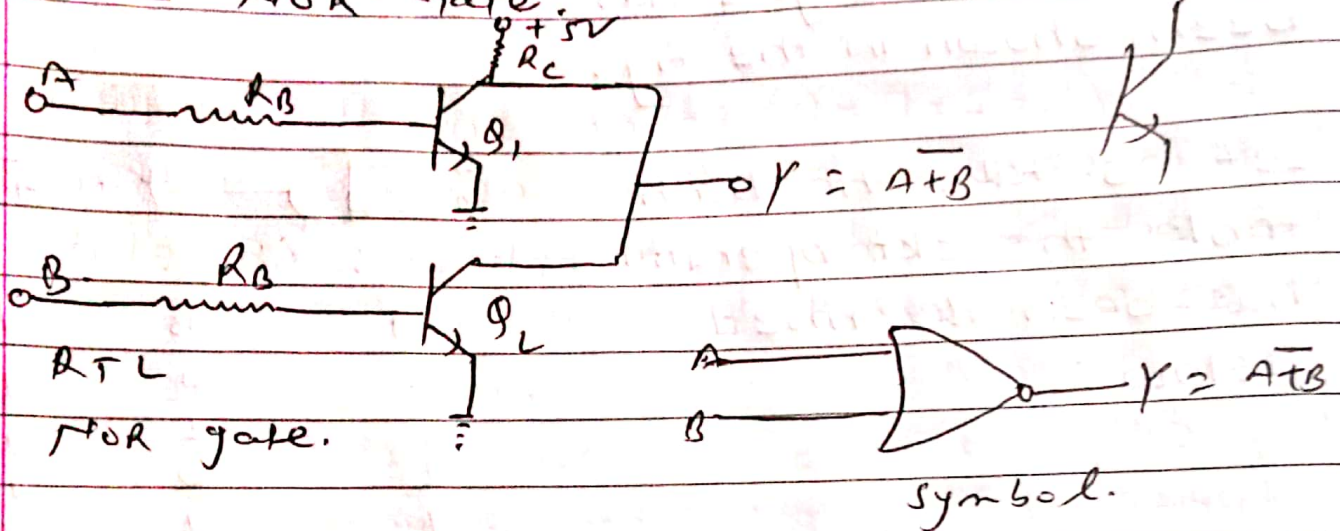
|  |   |   |   |
|--|---|---|---|
| For the first entry,   | A | B | Y |
| $A=0, B=0$ , no voltage drops across base resistors $R_B$ and hence both the transistors remain off. Hence the supply voltage across $R_C$ appears in the output and $Y=1$ . | 0 | 0 | 1 |
| For the 2 <sup>nd</sup> entry,   | 0 | 1 | 0 |
| $A=0, B=1$ , the upper transistor remains off while there is voltage drop across $R_B$ of the lower base resistor that biases  | 1 | 0 | 0 |
|  | 1 | 1 | 0 |



the voltage drop across  $R_c$  by passes to the ground yielding  $Y=0$ .

Hence the NAND gate

RTL NOR Gate:



The RTL ckt for the NOR gate has been outlined in the fig. The truth table for the NOR gate is given below:

For the first entry,  $A=0, B=0$ , no voltage drops across base resistors  $R_B$  and hence both the transistors remain off. Hence the supply voltage across  $R_c$  appears in the output and  $Y=1$ .

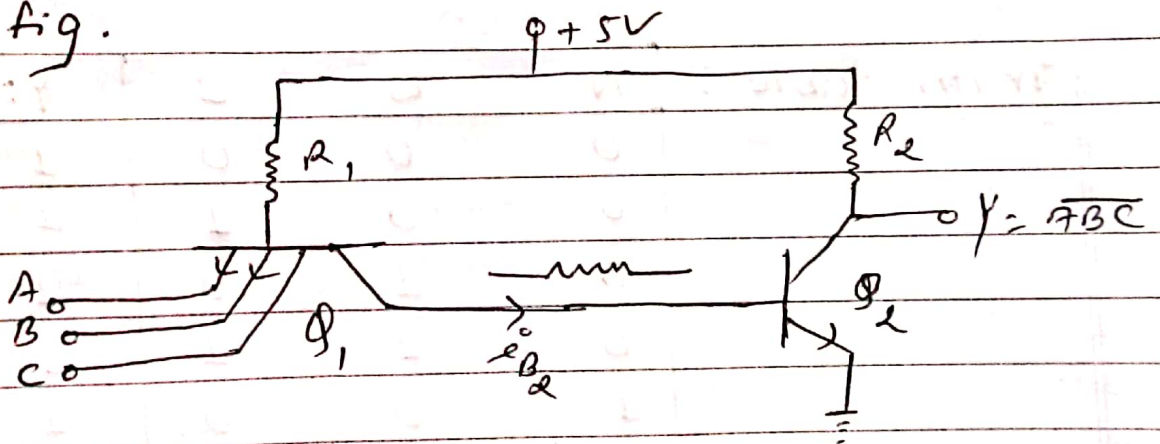
For the 2<sup>nd</sup> entry,  $A=0, B=1$ , the upper transistor remains off while there is voltage drop across  $R_B$  of the lower base resistor that biases



the lower transistor, it conducts and the supply voltage by passes thereby giving  $Y=0$ . For the 3<sup>rd</sup> entry  $A=1$ ,  $B=0$ , the same thing happens as in the 2<sup>nd</sup> entry. For the last entry  $A=1$ ,  $B=1$  both the transistors bias by the voltage drops across  $R_B$  and the supply voltage across  $R_C$  passes to the ground thereby giving  $Y=0$ . Hence the NOR gate.

### TTL NAND gate:

The TTL NAND ckt has been outlined in the fig.



$Q_1$  is the transistor with multiple emitter inputs ( $A, B, C$ ). When one of the inputs ( $A$  or  $B$  or  $C$ ) is low, the supply voltage drop across  $R_1$  biases the PN junction of Base-emitter of  $Q_1$  and passes to the ground. Hence  $Q_2$  is unbiased, it remains OFF and the voltage seeing across  $R_2$



appears in the output i.e.  $Y = 1$ .

When any two of the inputs or all the inputs are low, the same situation appears as described above and hence  $Y = 1$  again.

When all the inputs ( $A = B = C = 1$ ), the base-emitter junction of  $Q_1$  is reverse biased while Base-collector junction of the same transistor is forward biased. Hence transistor  $Q_2$  remains forward biased and the supply voltage across  $R_C$  goes to the ground thereby ~~providi~~ producing a low output i.e.  $Y = 0$ .

Truth table :

| A | B | C | $Y = \overline{ABC}$ |
|---|---|---|----------------------|
| 0 | 0 | 0 | 1                    |
| 0 | 0 | 1 | 1                    |
| 0 | 1 | 0 | 1                    |
| 0 | 1 | 1 | 1                    |
| 1 | 0 | 0 | 1                    |
| 1 | 0 | 1 | 1                    |
| 1 | 1 | 0 | 1                    |
| 1 | 1 | 1 | 0                    |